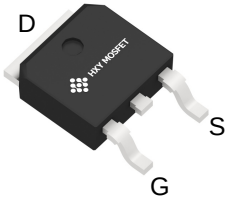
FQD10N20CTM_F080

N-Channel Enhancement Mode MOSFET

Description

The FQD10N20CTM_F080 can be used in various power swithching circuit for system miniaturization and higher efficiency.The package form is TO-252-2L, which accords with the RoHS standard.

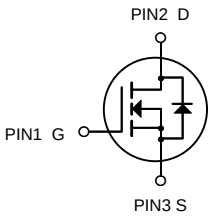


TO-252-2L

General Features

V_{DS} = 200V I_D =9A

$R_{DS(ON)}$ < 270mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
FQD10N20CTM_F080	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V	9	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V	5.7	A
I_{AS}	Avalanche Current	9	A
P_D@T_C=25°C	Total Power Dissipation	72	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Electrical Characteristics (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	200	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=200V, V_{GS}=0V	---	---	1	μA
		V_{DS}=160V, V_{GS}=0V,Tc=125	---	---	10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V, V_{DS}=0A	---	---	±100	nA
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	2	---	4	V
$R_{DS(ON)}$	Drain-Source On Resistanc	V_{GS}=10V,I_D=4.5A	---	0.235	0.27	Ω
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1MHz	---	720	920	pF
C_{oss}	Output Capacitance		---	85	110	
C_{rss}	Reverse Transfer Capacitance		---	22	29	
$t_{d(on)}$	Turn-On Delay Time[3,4]	VDD=100V , VGS=10V , RG=25Ω， I_D=9A	---	10	23	ns
t_r	Rise Time[3,4]		---	69	138	ns
$t_{d(off)}$	Turn-Off Delay Time[3,4]		---	59	118	ns
t_f	Fall Time[3,4]		---	63	128	ns
Q_g	Total Gate Charge[3,4]	V_{GS}=10V, V_{DS}=160V, I_D=9A	---	21	28	nC
Q_{gs}	Gate-Source Charge[3,4]		---	3.8	---	nC
Q_{gd}	Gate-Drain “Miller” Charge[3,4]		---	11	---	nC
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	9	A
I_{SM}	Pulsed Source Current		---	---	36	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=9A , T_J=25°C	---	---	1.45	V
Trr	Reverse Recovery Time	IF=9A , dI/dt=100A/μs , T_J=25℃	---	140	---	ns
Qrr	Reverse Recovery Charge		---	2.2	---	nC

Notes:

1, L=8mH, IAS=9A, VDD=50V, RG=25Ω, Starting TJ =25°C

2, Repetitive Rating : Pulse width limited by maximum junction temperature

3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

4, Essentially Independent of Operating Temperature

Typical Characteristics (T_A=25°C unless otherwise noted)

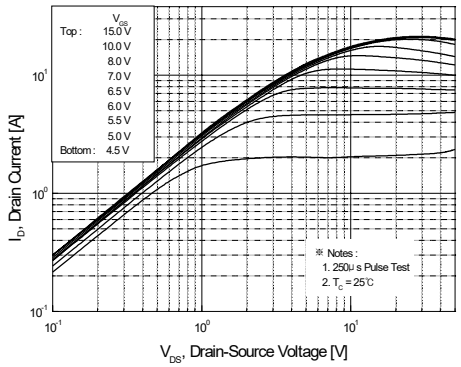


Figure 1. On-Region Characteristics

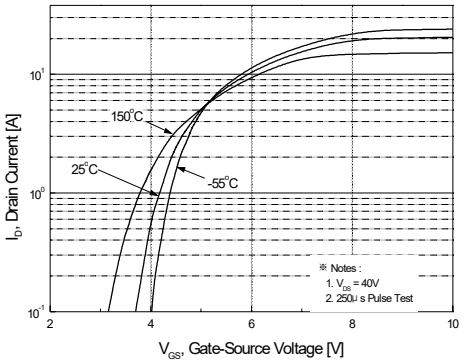


Figure 2. Transfer Characteristics

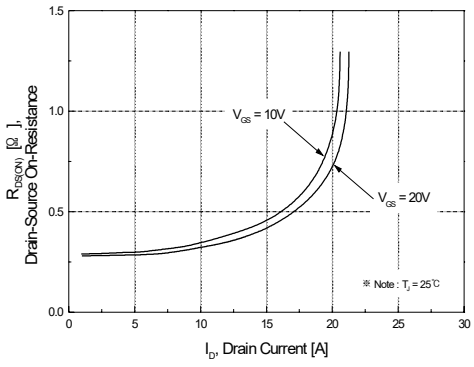


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

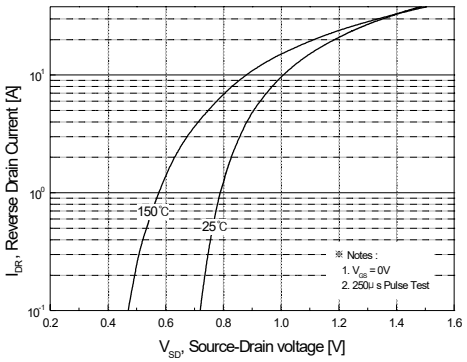


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

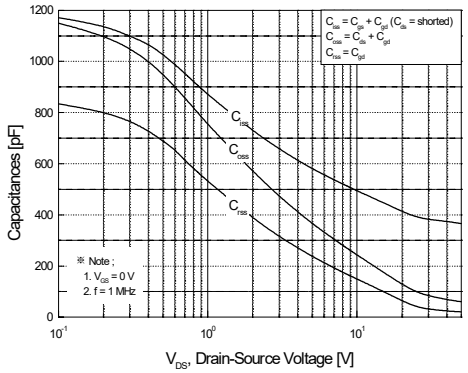


Figure 5. Capacitance Characteristics

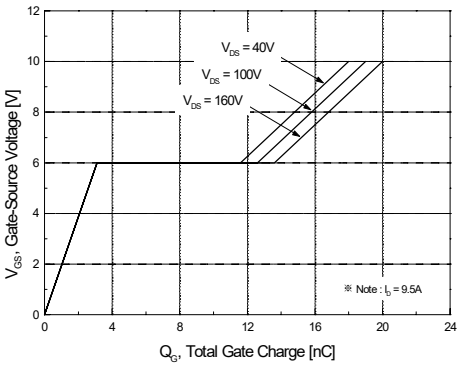


Figure 6. Gate Charge Characteristics

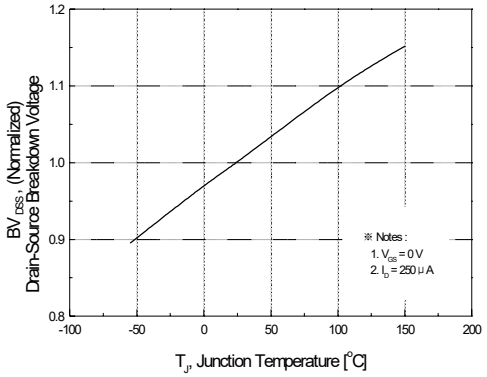


Figure 7. Breakdown Voltage Variation vs Temperature

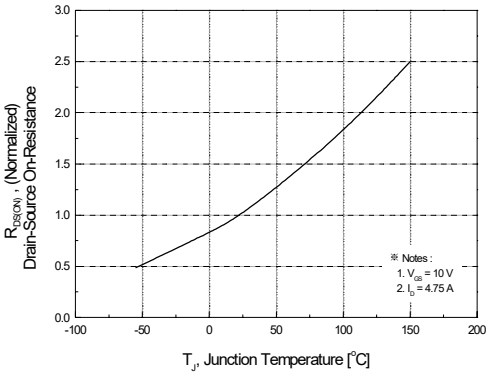


Figure 8. On-Resistance Variation vs Temperature

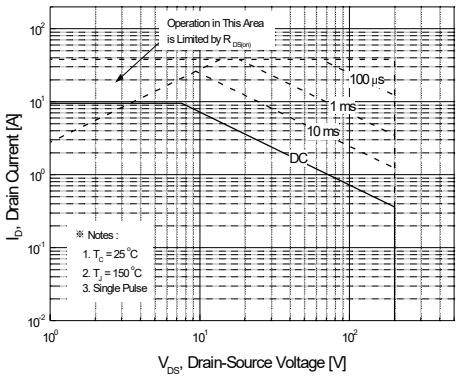


Figure 9-1. Maximum Safe Operating Area

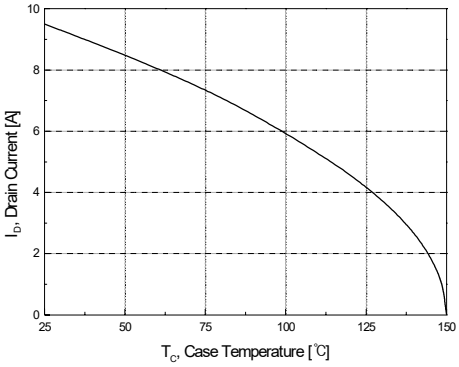


Figure 10. Maximum Drain Current vs Case Temperature

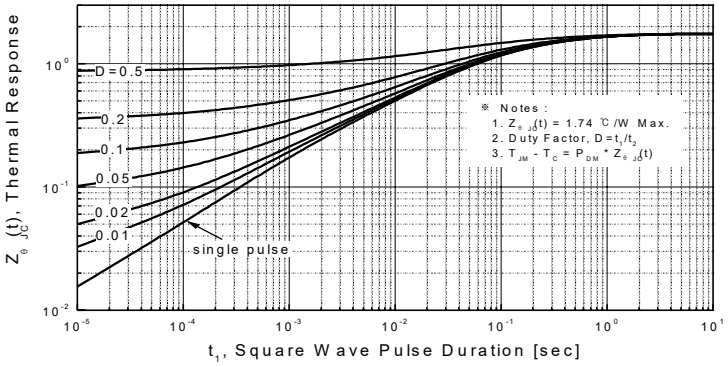
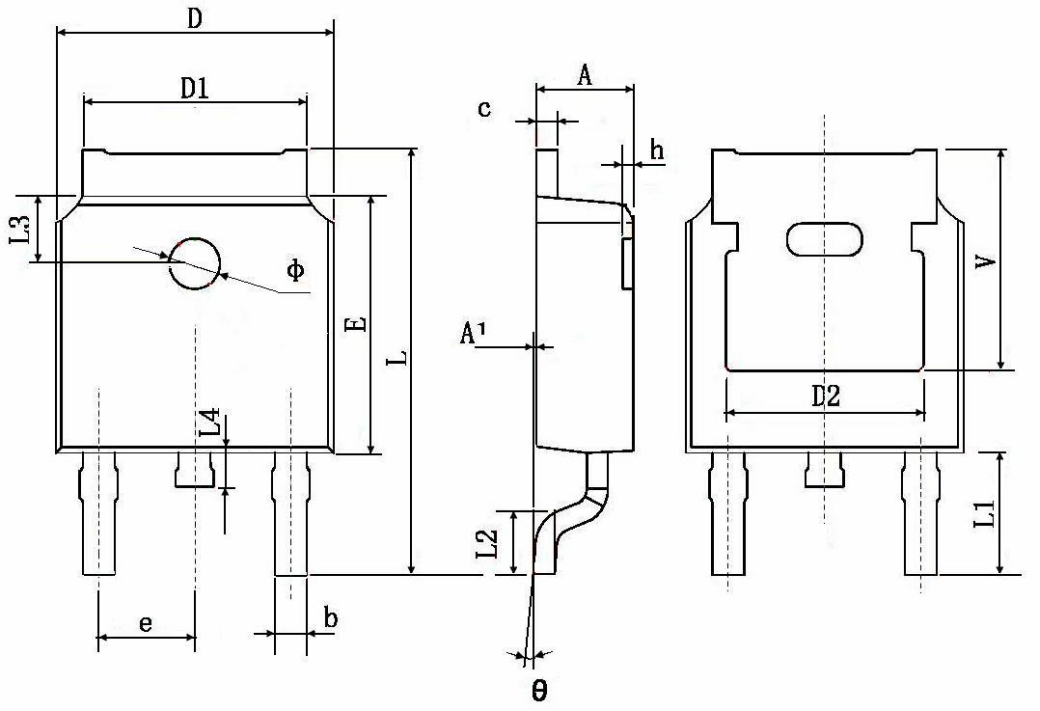


Figure 11-1. Transient Thermal Response Curve

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

Attention

■ Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.

■ HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

■ Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer’s products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer’s products or equipment.

■ HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could
give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.